

Cryogenic Performance of NGC 35nm InP Low Noise Amplifiers

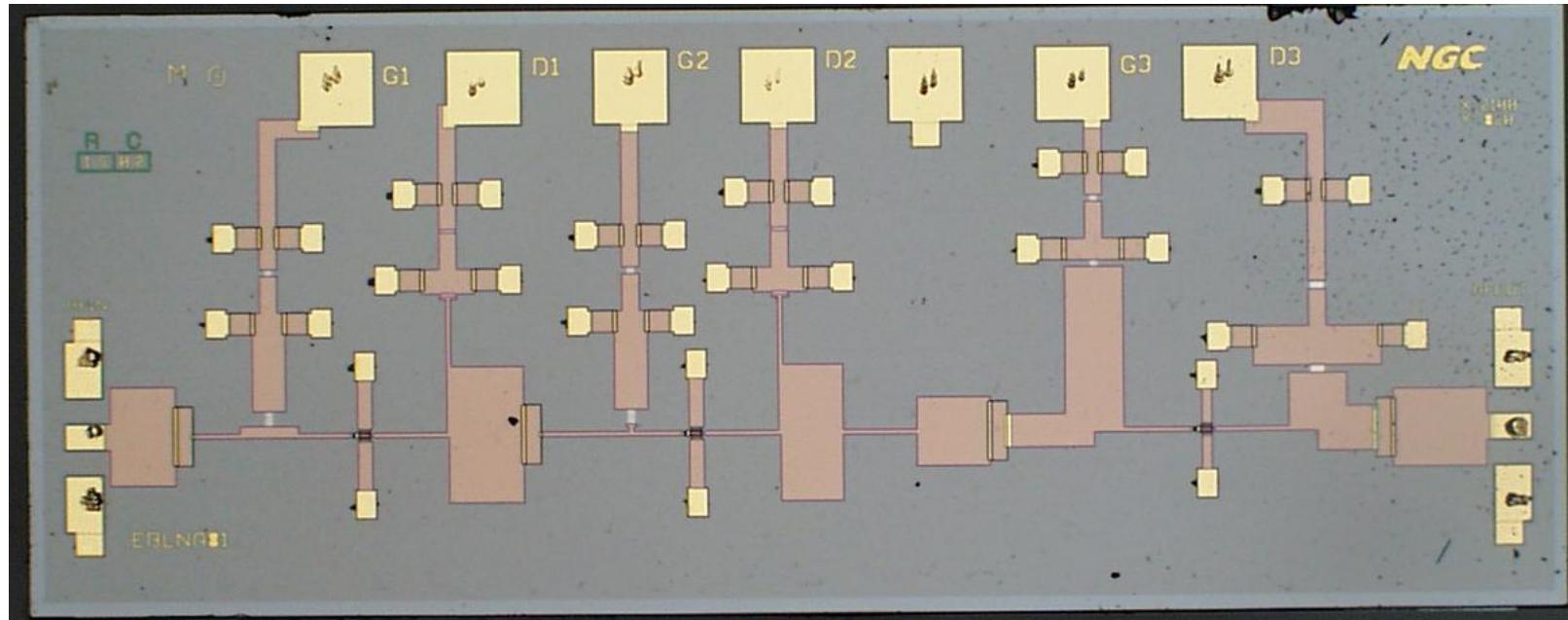


Eric W. Bryerton

Atacama Large Millimeter/submillimeter Array
Expanded Very Large Array
Robert C. Byrd Green Bank Telescope
Very Long Baseline Array



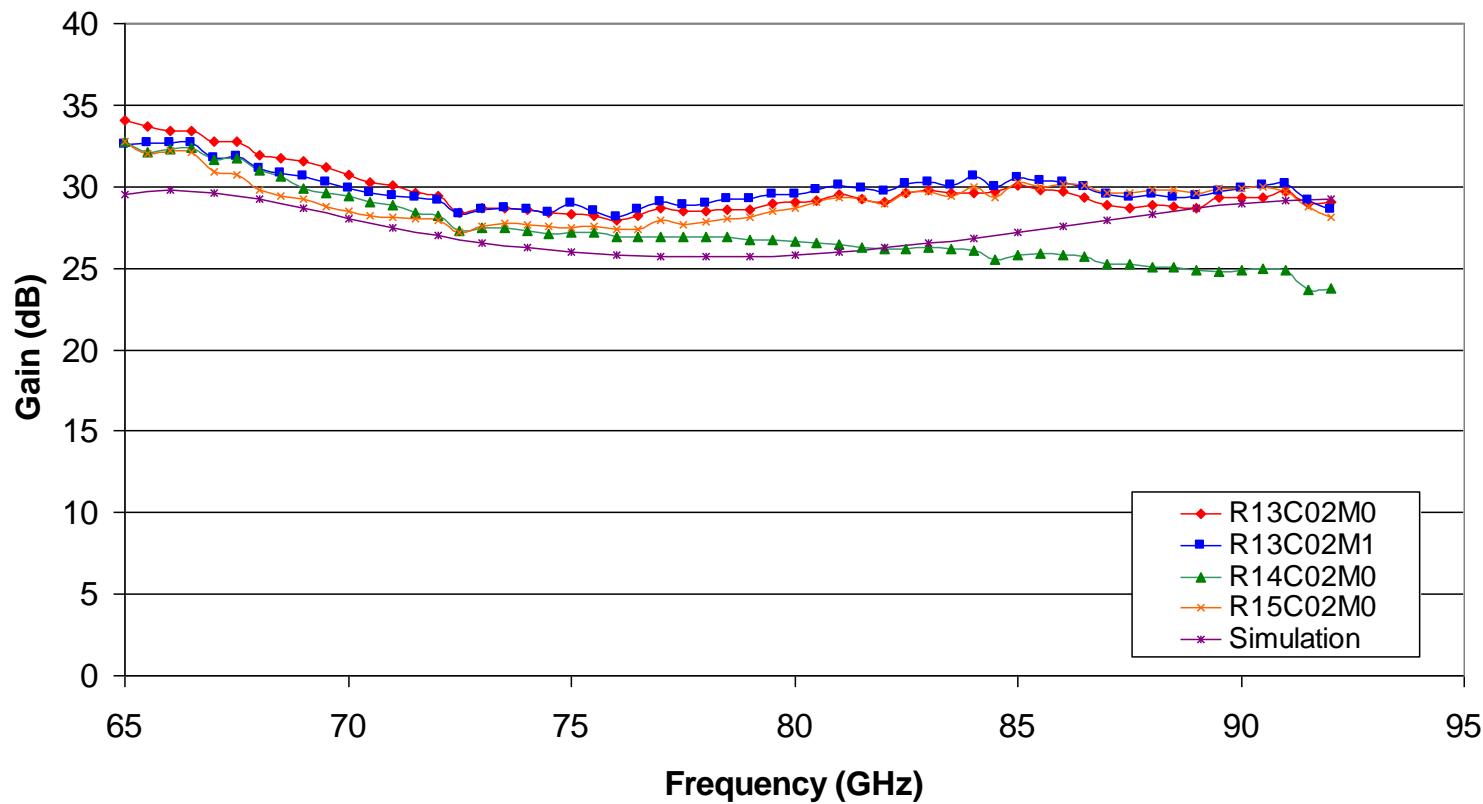
EBLNA8 I



- Wafer run complete 1/15/2008
- Chip Dimension: 2.1mm x 0.8mm

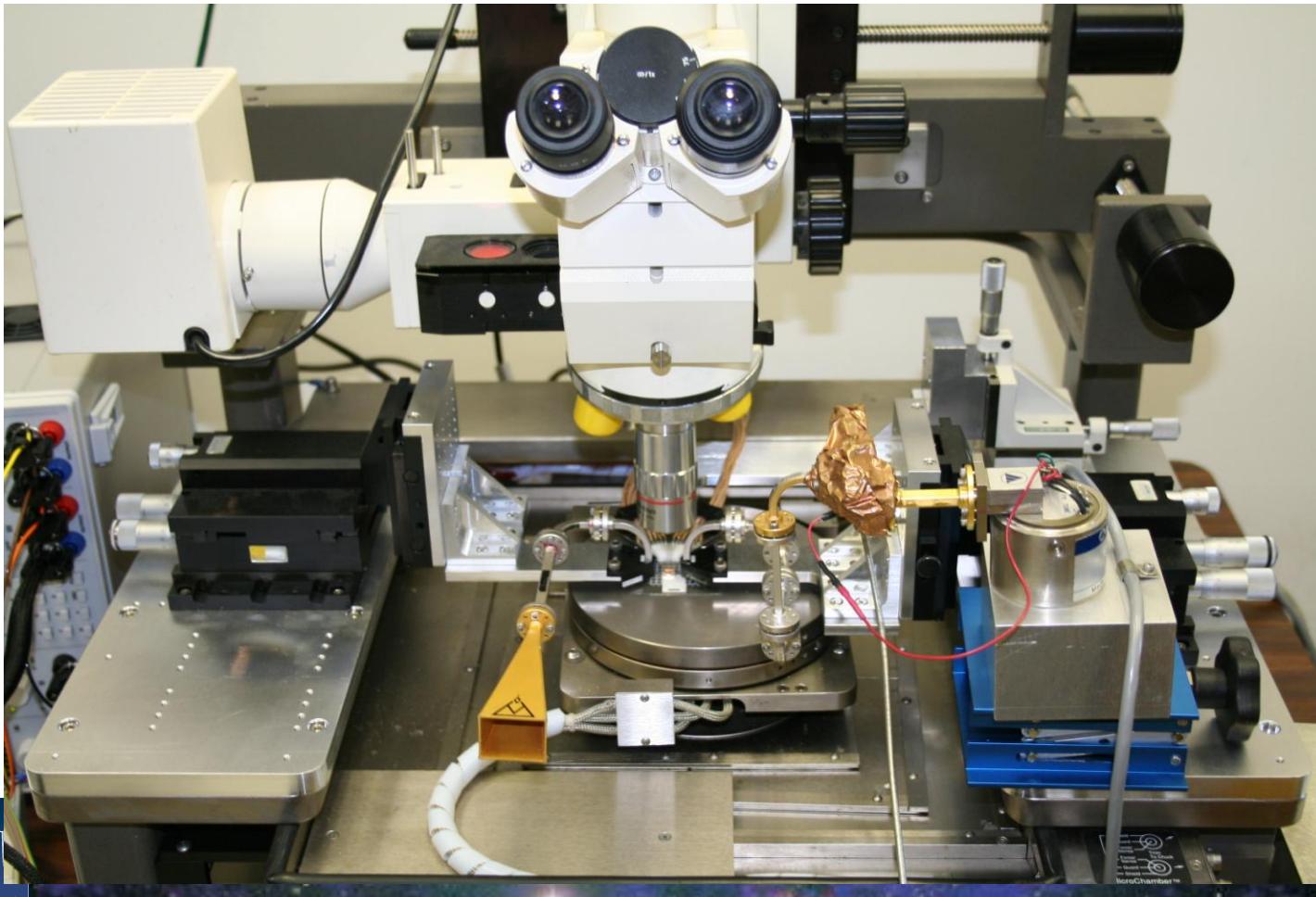
On-chip Measurements

EBLNA81 (VG=+0.3V, VD=1.2V)
On-wafer, T=297K



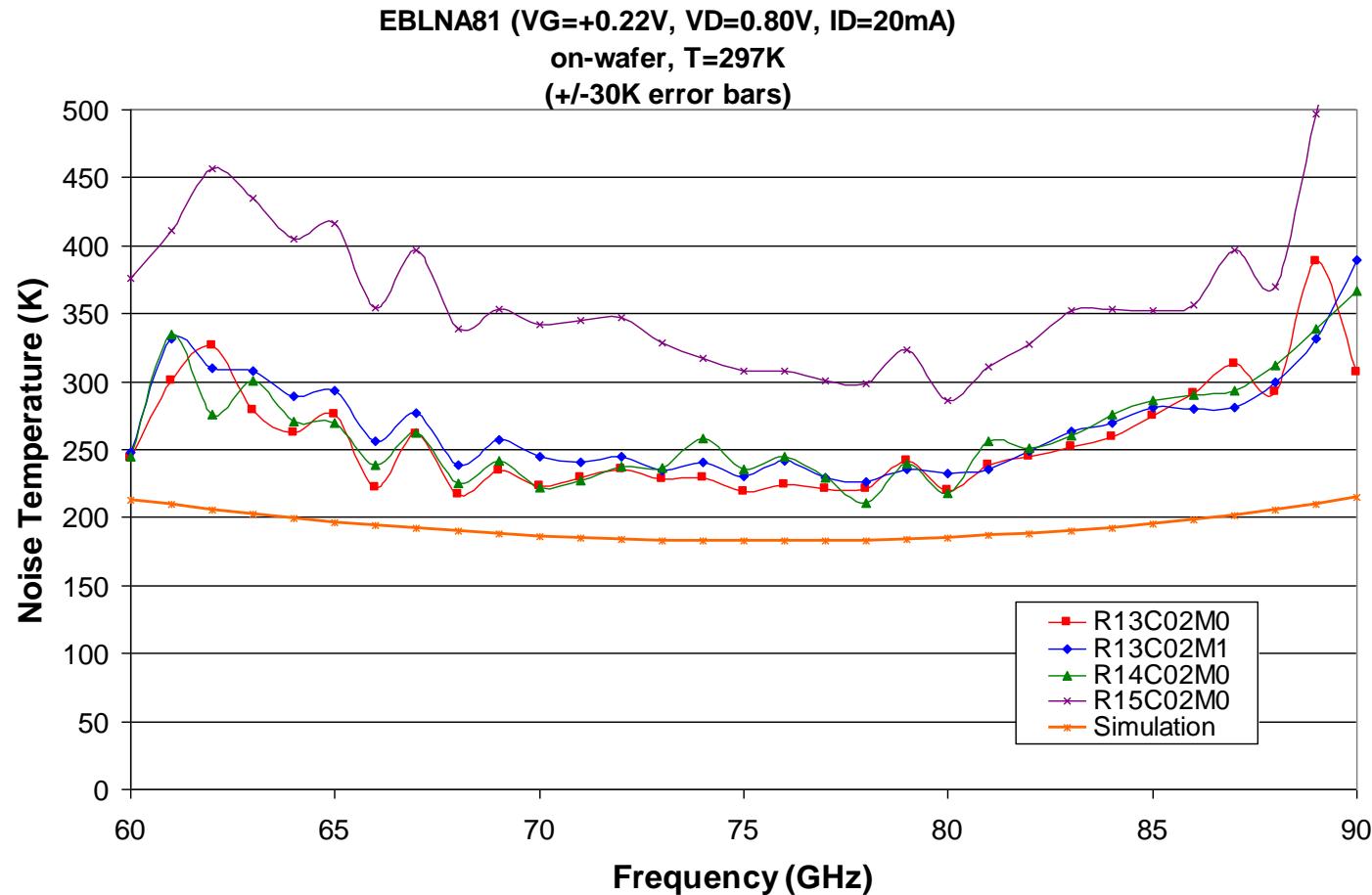
- G_m increased in simulation (from 1950 to 2500 mS/mm) to match measured performance

On-Chip Noise Measurement

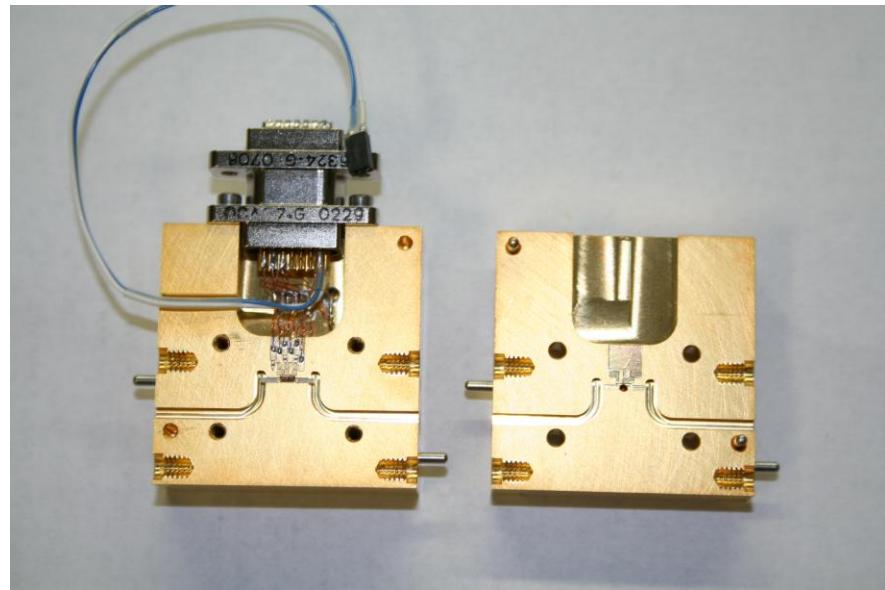
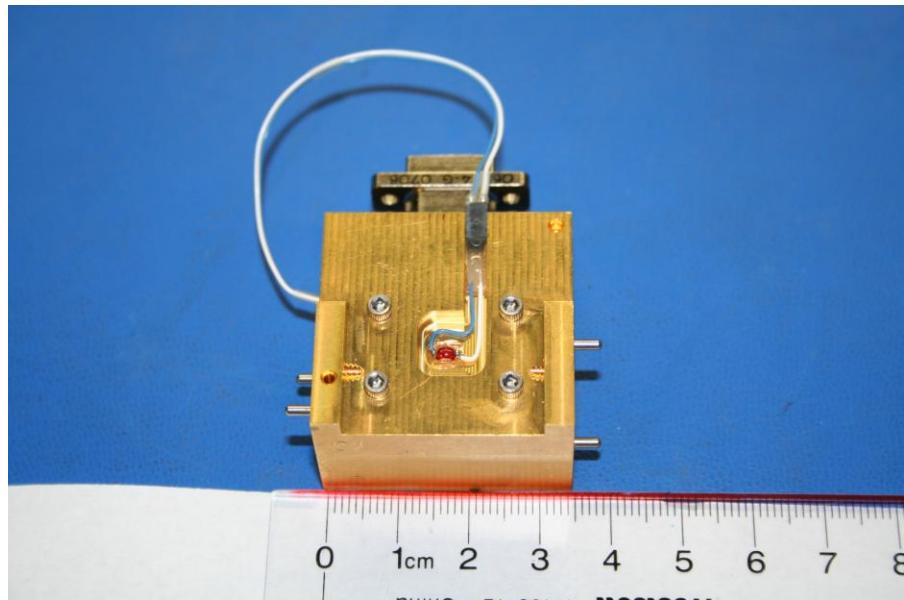


Cryogenic Performance of 35nm InP LNAs

On-chip Noise Measurement

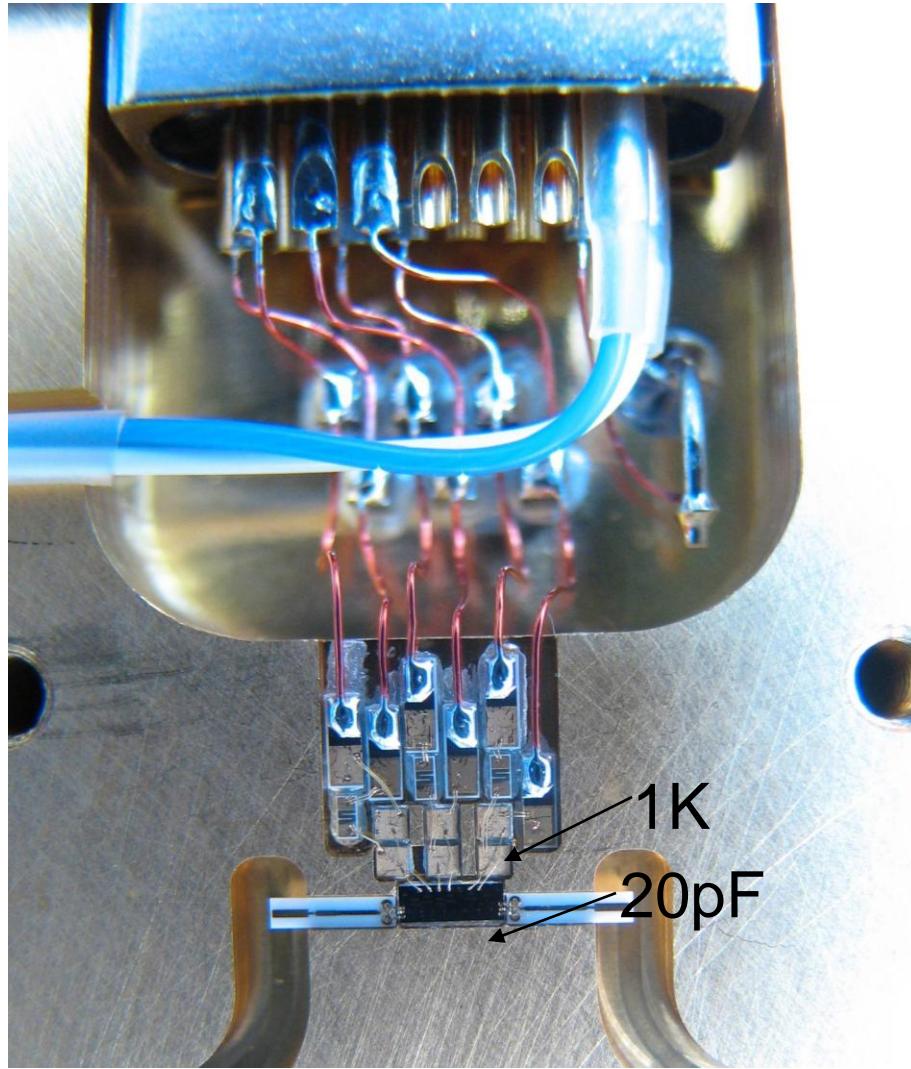


WR-12 LNA Module

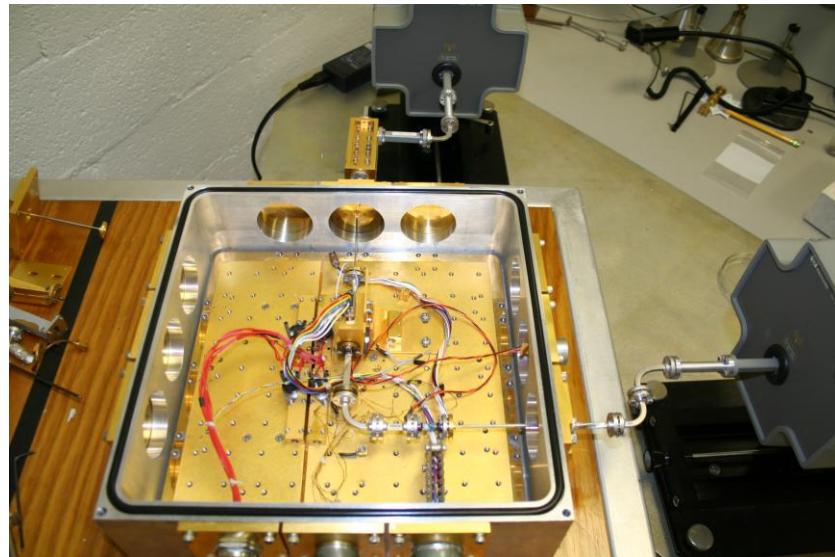


- Same MDM-15 pinout as CDL LNAs

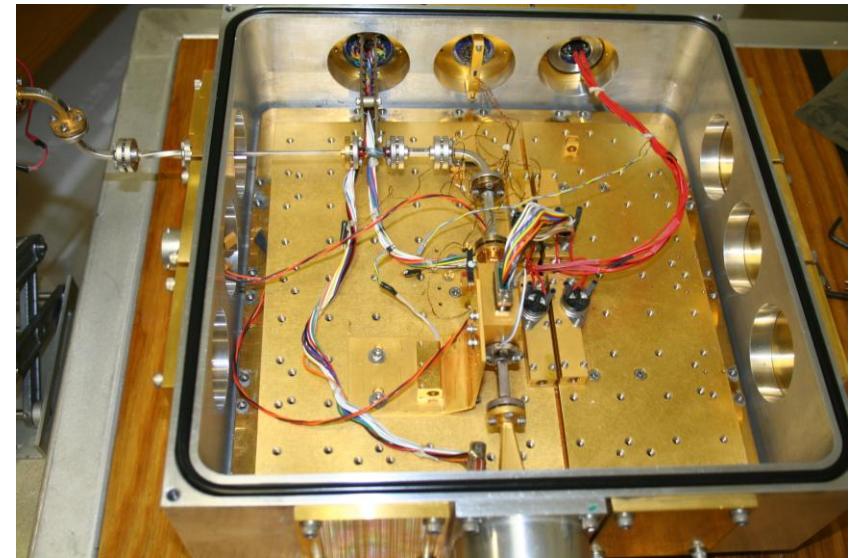
WR-12 LNA Module



LNA Module Measurements



S21

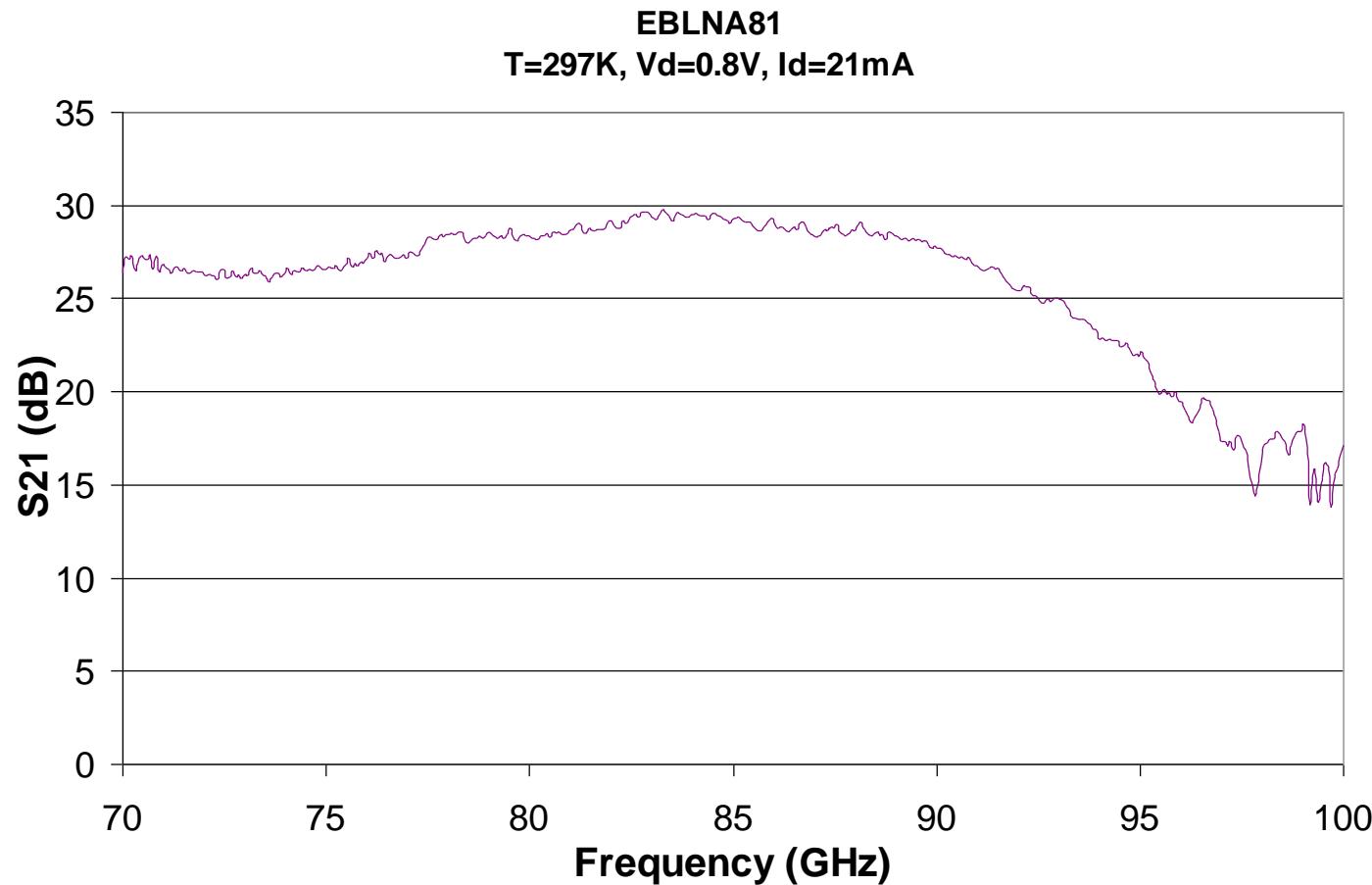


Noise

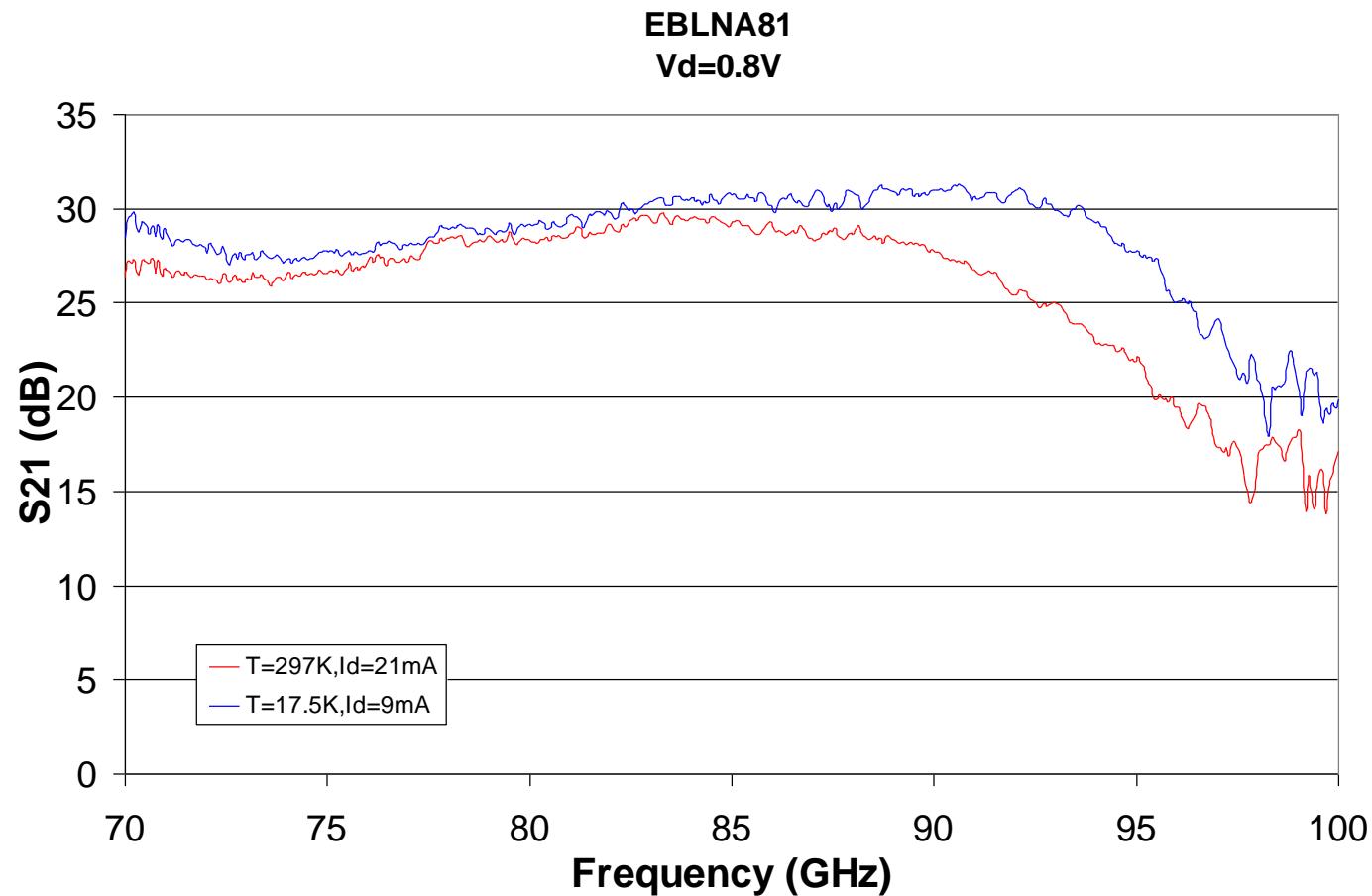


Cryogenic Performance of 35nm InP LNAs

LNA Module Measurements

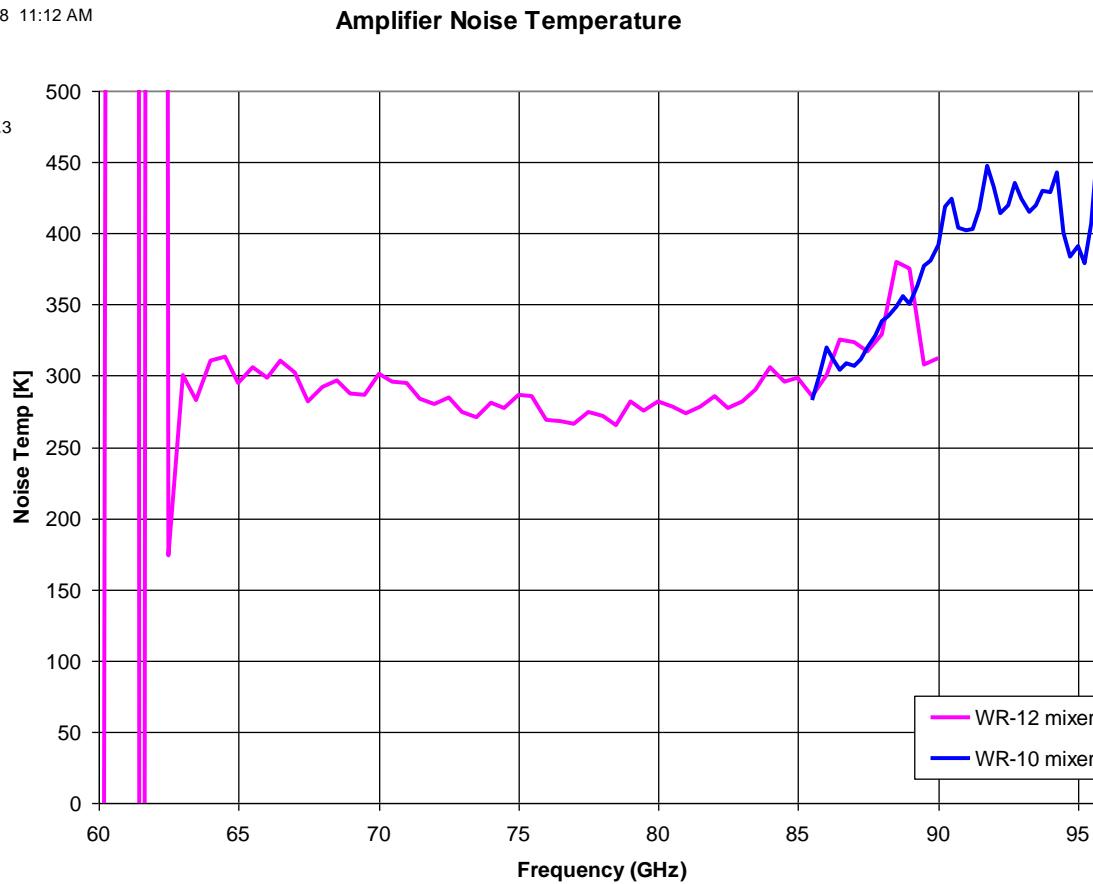


LNA Module Measurements



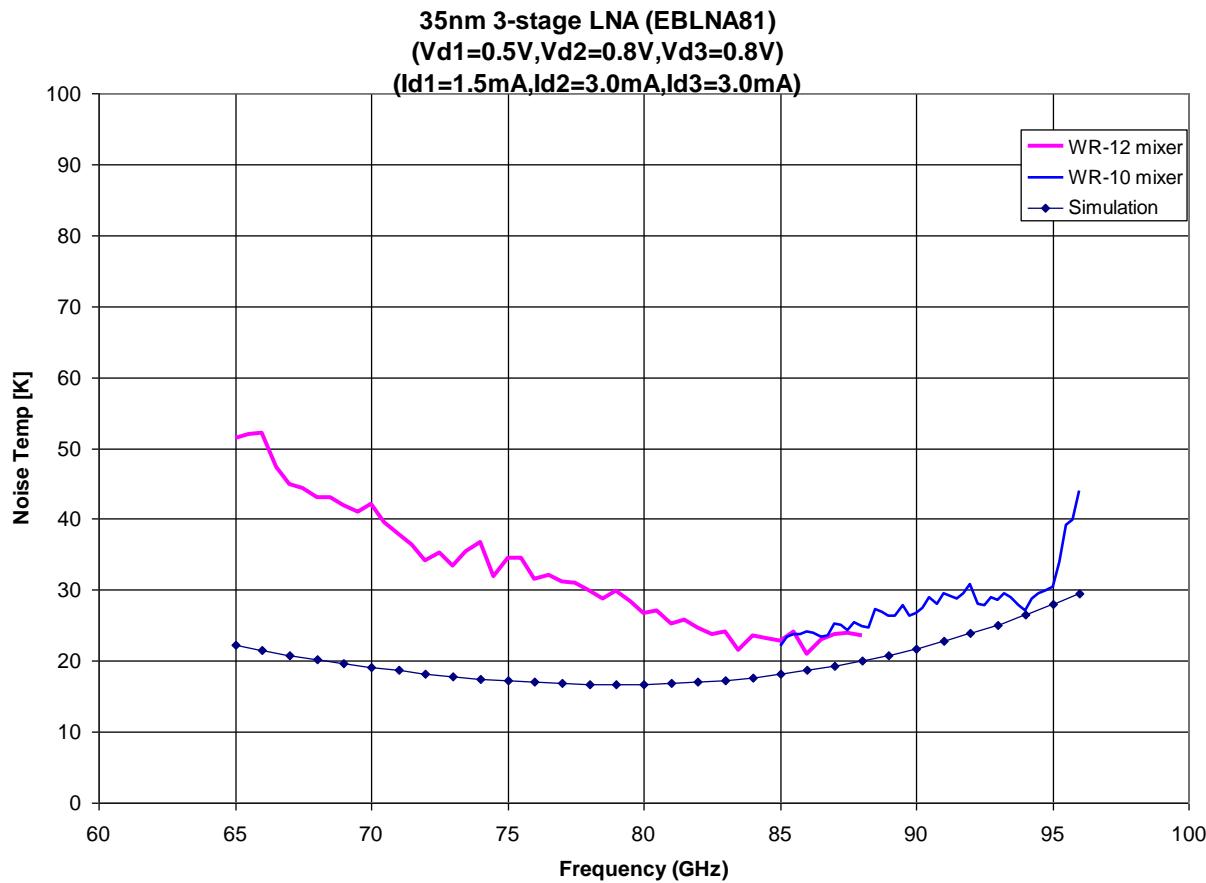
LNA Module Measurements

Amplifier ID: eblna81
Timestamp: 7/9/2008 11:12 AM
Measured by:
Dewar Temp: 327
Ambient Temp: 327
Noise Diode: 11833
Software Version: 1.3



$V_d=0.8V$, $I_d=7mA/\text{stage}$

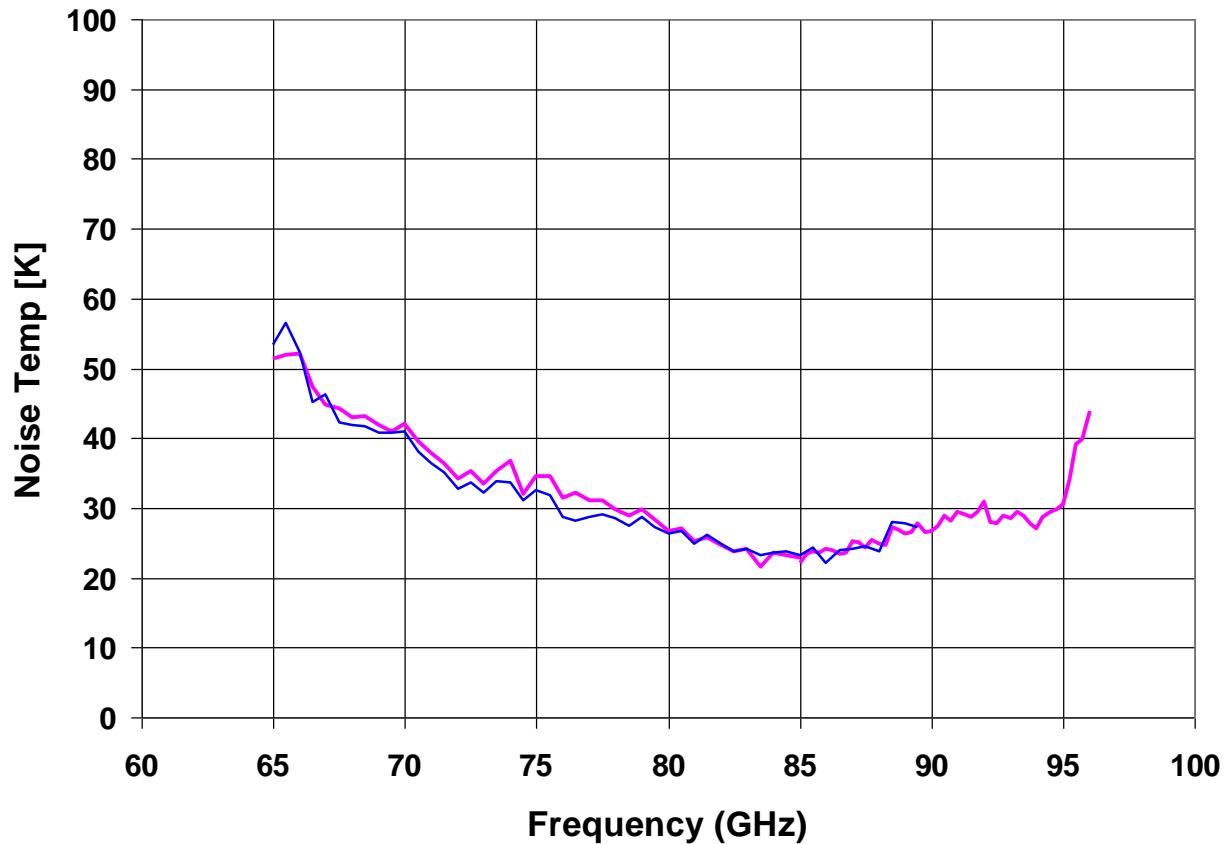
LNA Module Measurements



- Simulation: $G_m=2500\text{mS/mm}$, $I_{gs}=0$, $T_{drain}=1400$
- $P_{diss} = 5.55\text{mW}$

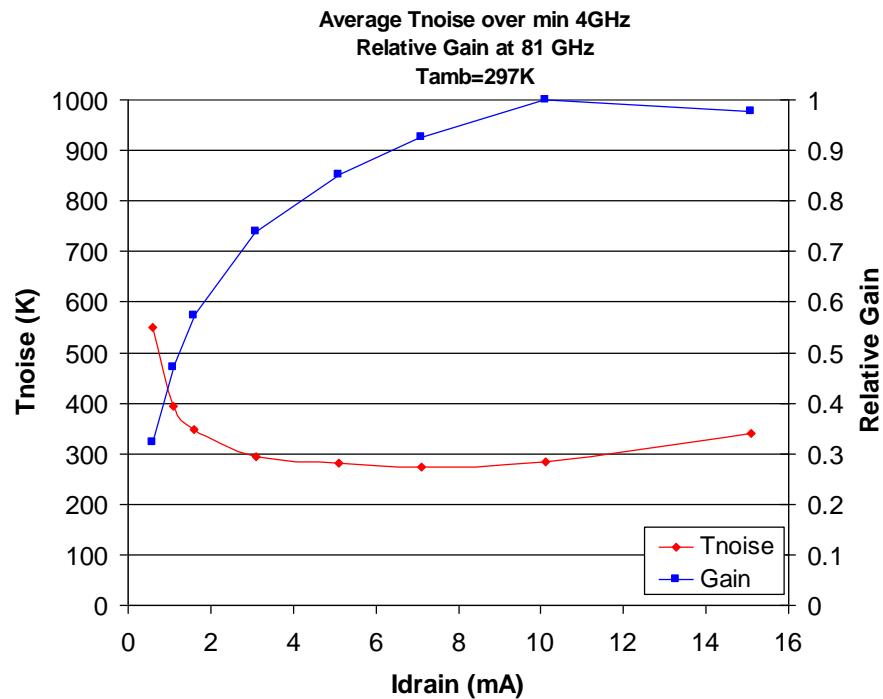
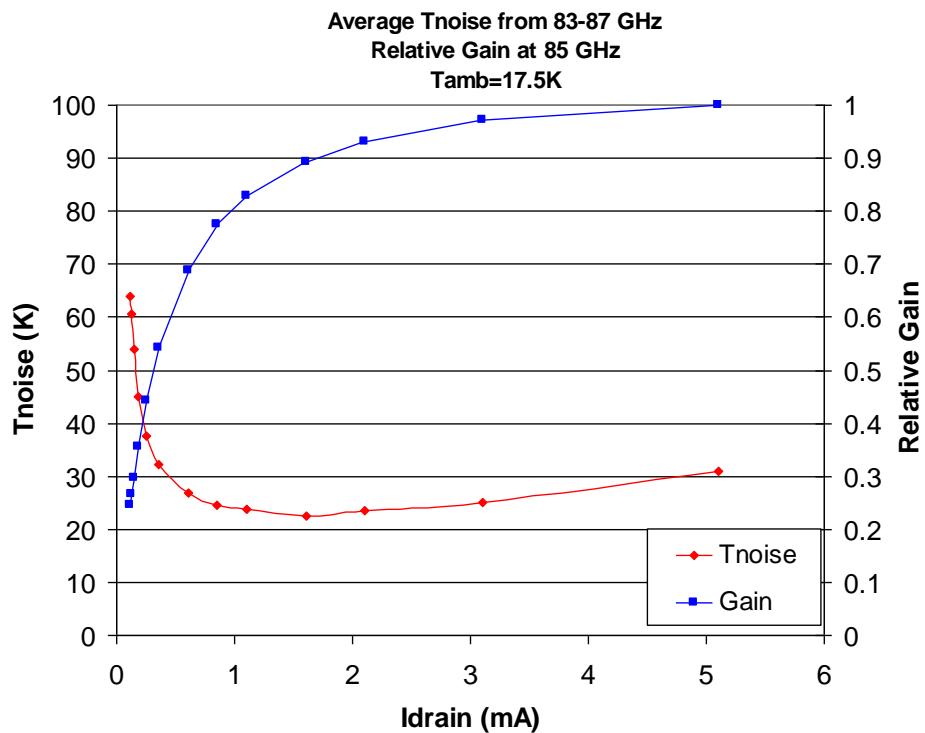
LNA Module Measurements

35nm 3-stage LNA (EBLNA81)

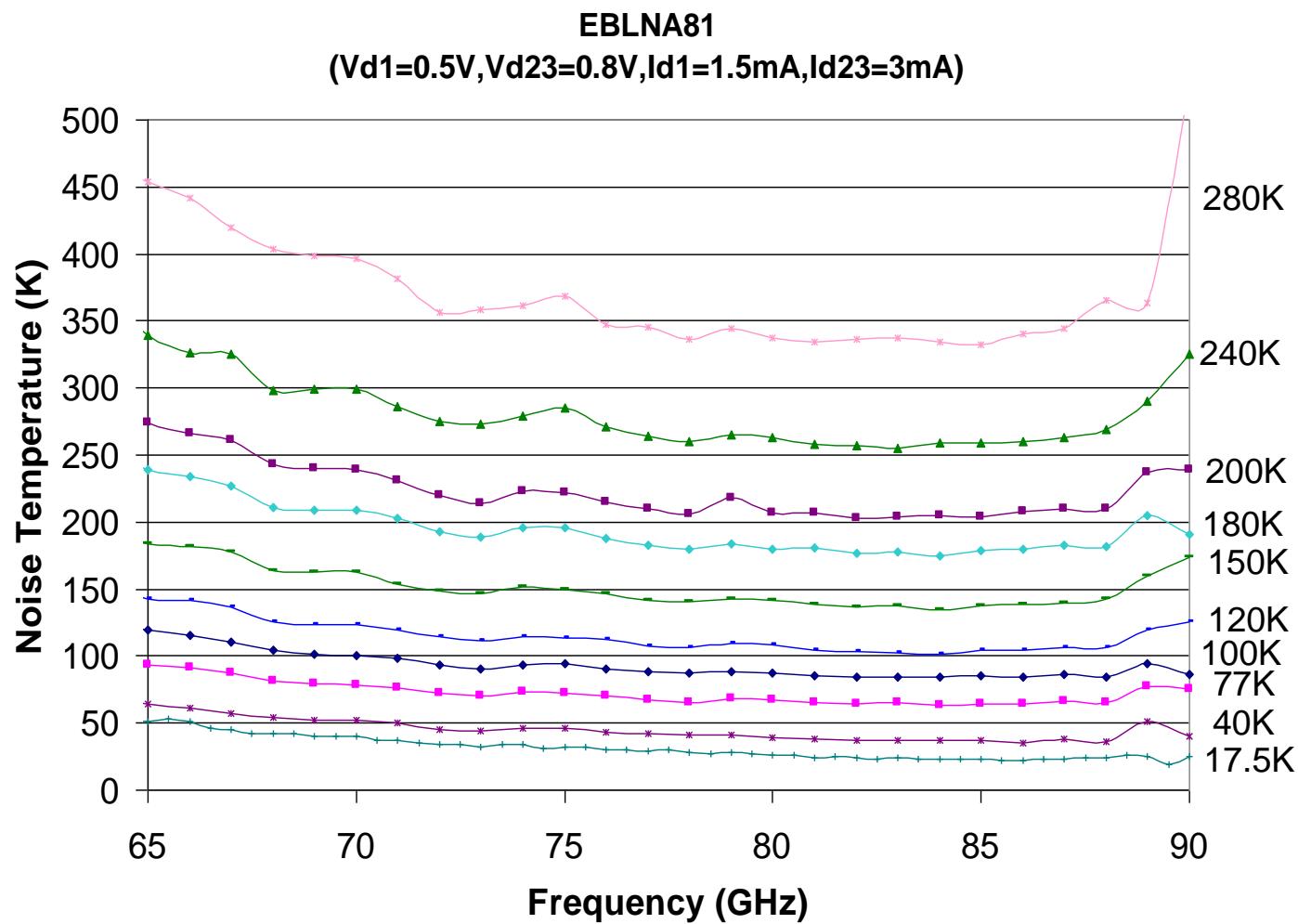


- Blue trace shows noise for minimum power dissipation:
 $V_{d1}=0.35V$, $V_{d23}=0.5V$, $I_d=4.5mA \rightarrow P_{diss} = 2.06mW$

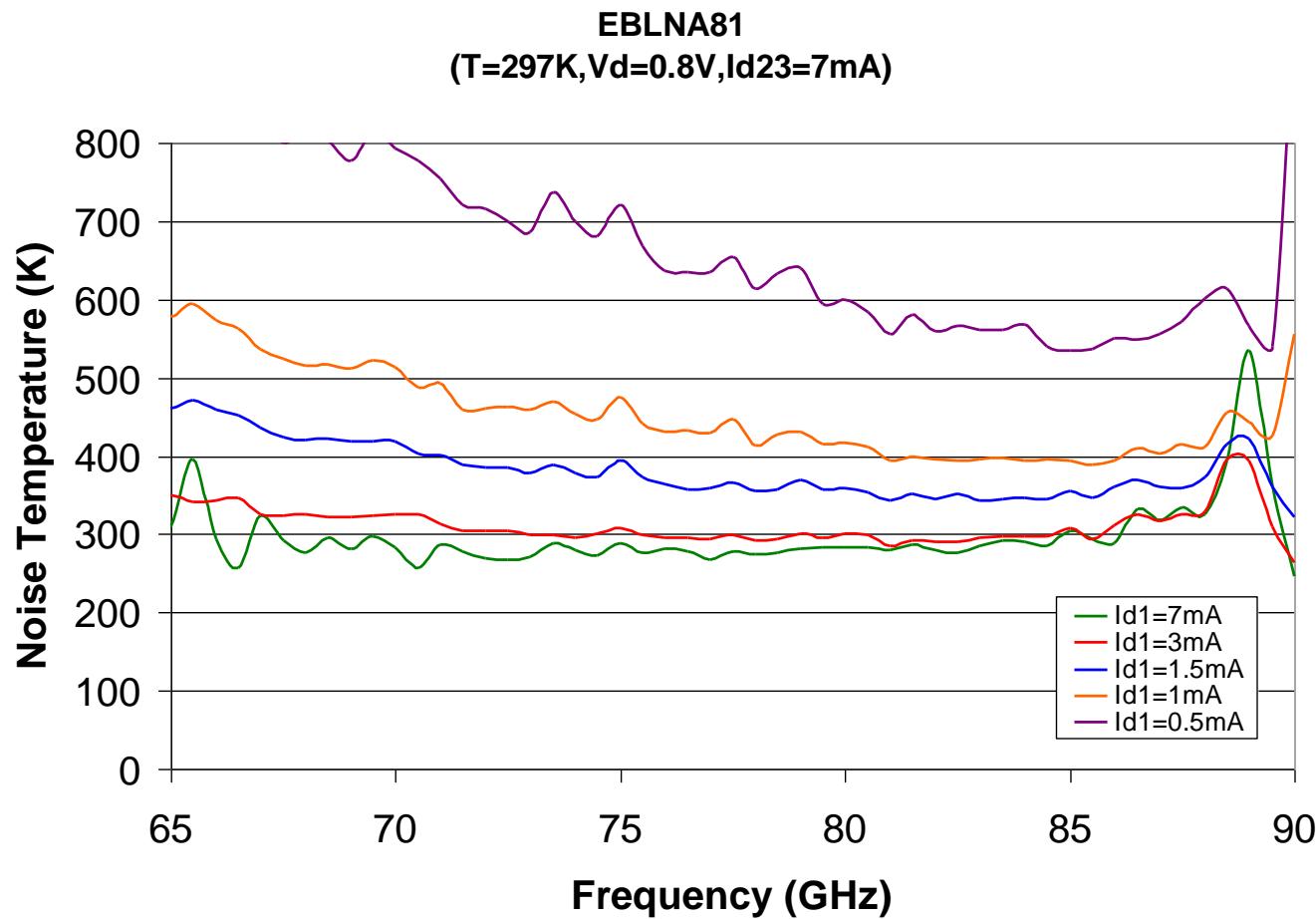
Pinchoff Characteristics



Why the frequency shift cold?

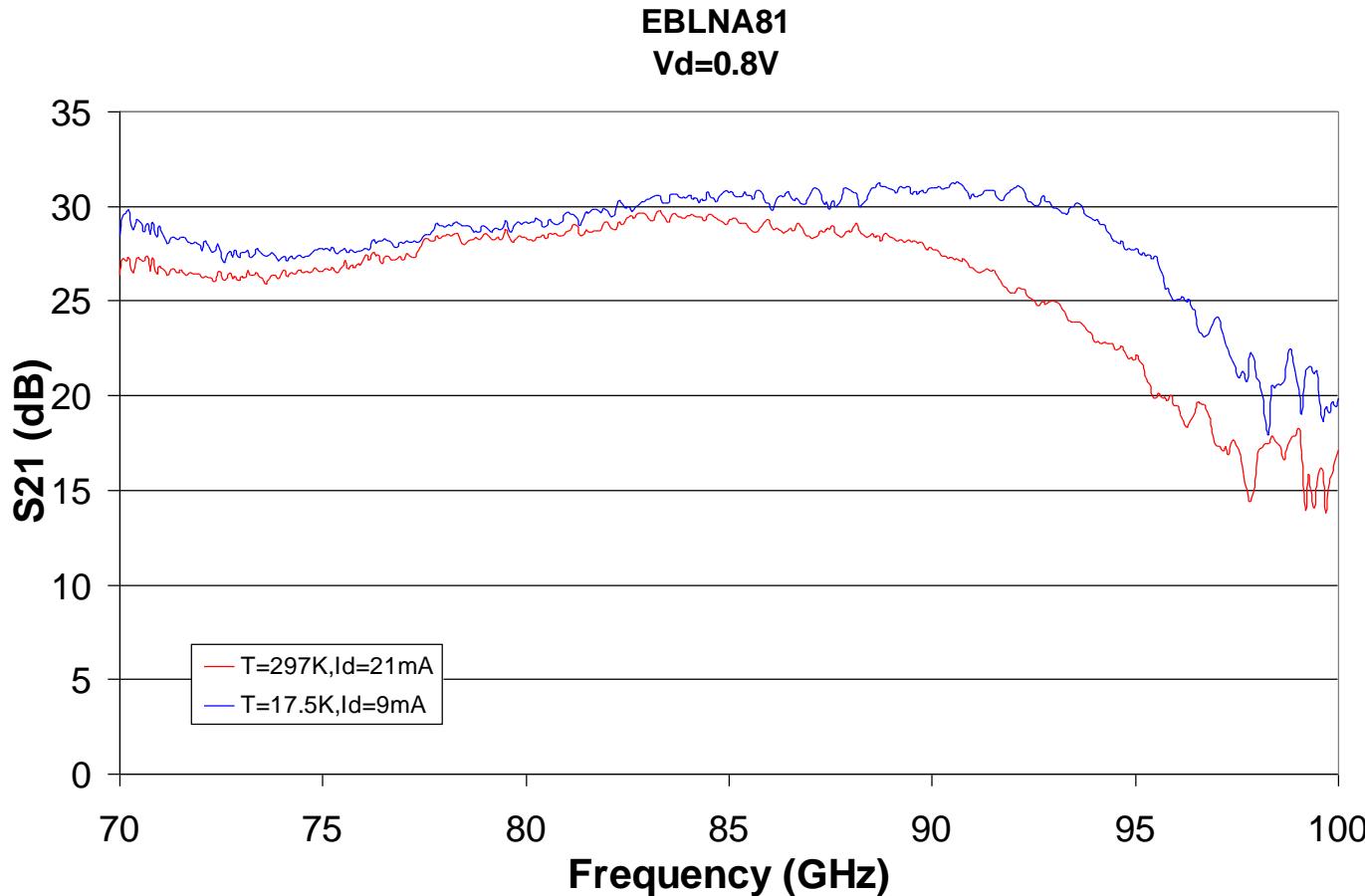


Why the frequency shift cold?



- Hypothesis: $C_{gs}(V_{gs})$ is causing frequency shift

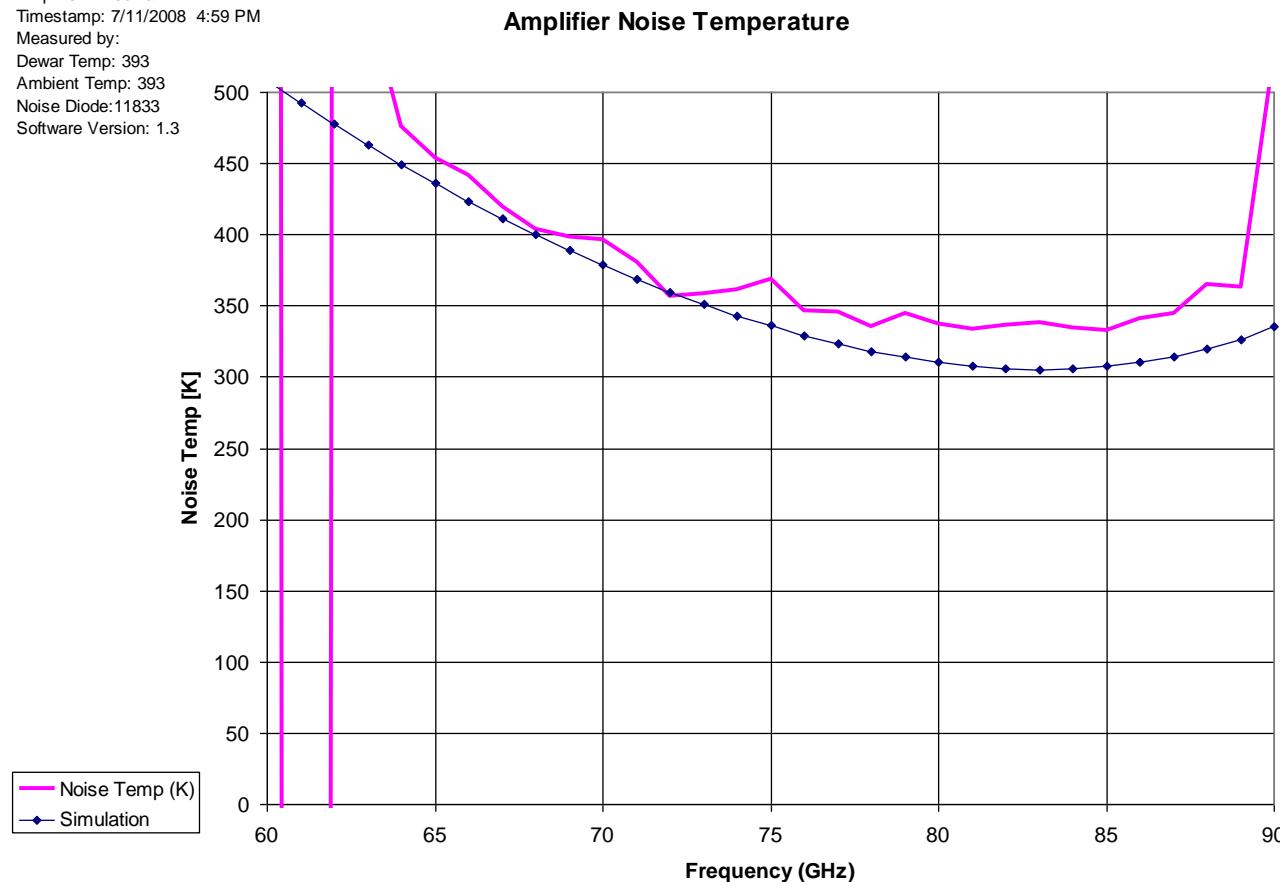
Revised cryogenic model for parasitics



- Change in S_{21} also modeled well by decrease in C_{gs}

Revised cryogenic model for parasitics

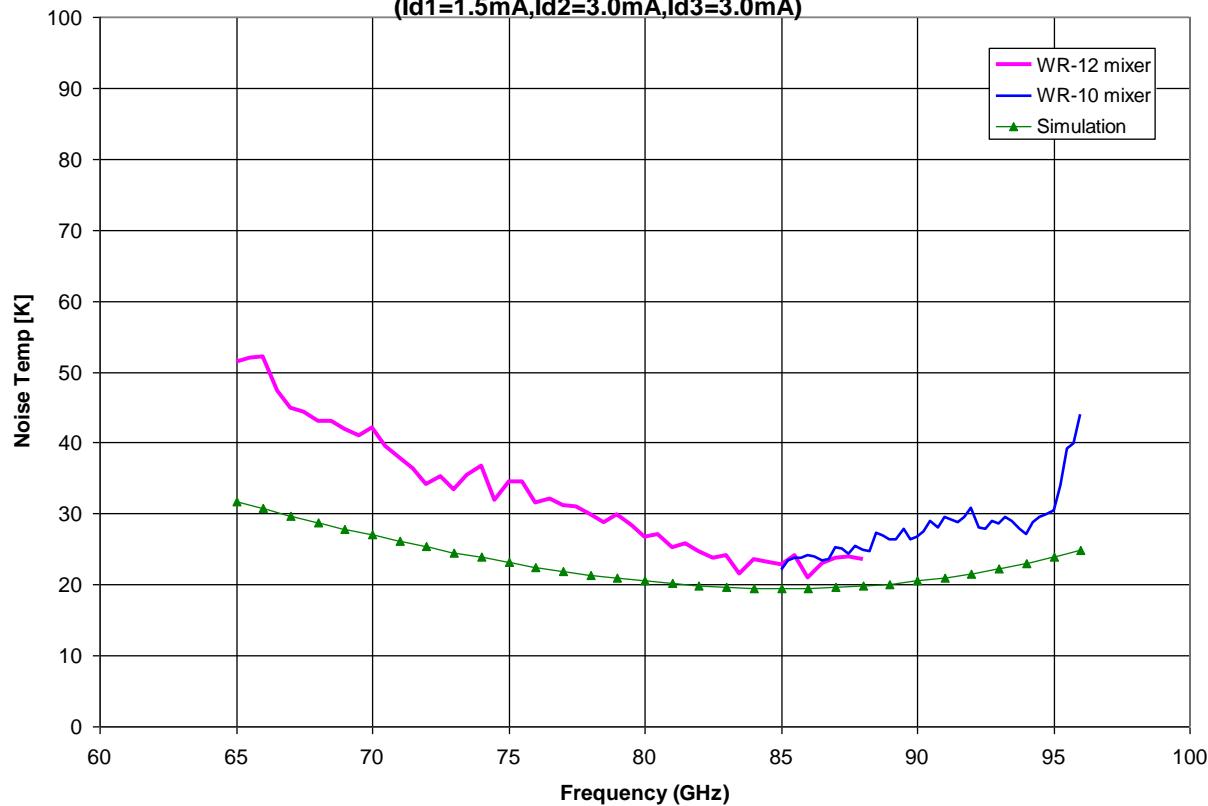
Amplifier ID: eblna1
Timestamp: 7/11/2008 4:59 PM
Measured by:
Dewar Temp: 393
Ambient Temp: 393
Noise Diode: 11833
Software Version: 1.3



- $I_d1=1.5\text{mA}$
- Simulation: $gm1=33.6\text{mS}$, $gm23=66.6\text{mS}$, $Cgs1=12.6\text{fF}$ (versus 17.5fF in original model)

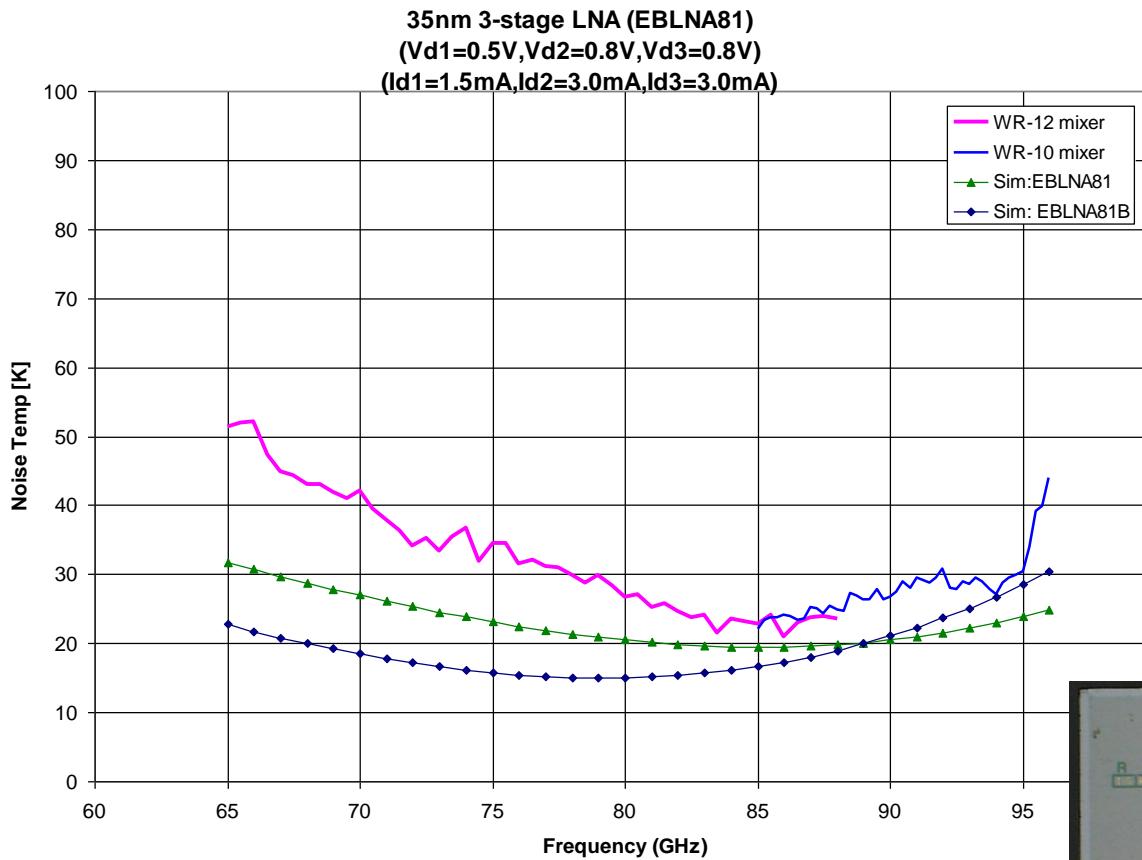
Revised cryogenic model for parasitics

35nm 3-stage LNA (EBLNA81)
(Vd1=0.5V, Vd2=0.8V, Vd3=0.8V)
(Id1=1.5mA, Id2=3.0mA, Id3=3.0mA)



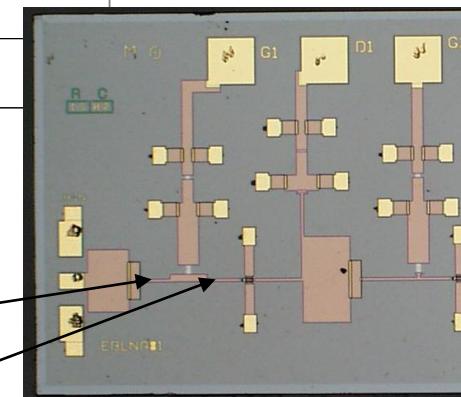
- Simulation: Gm1=64mS, Gm23=90mS, Td1=1400K, Td23=2800K, Cgs1=12.6fF (compared to 17.5fF original)

EBLNA81B: Retuned for 67-90 GHz

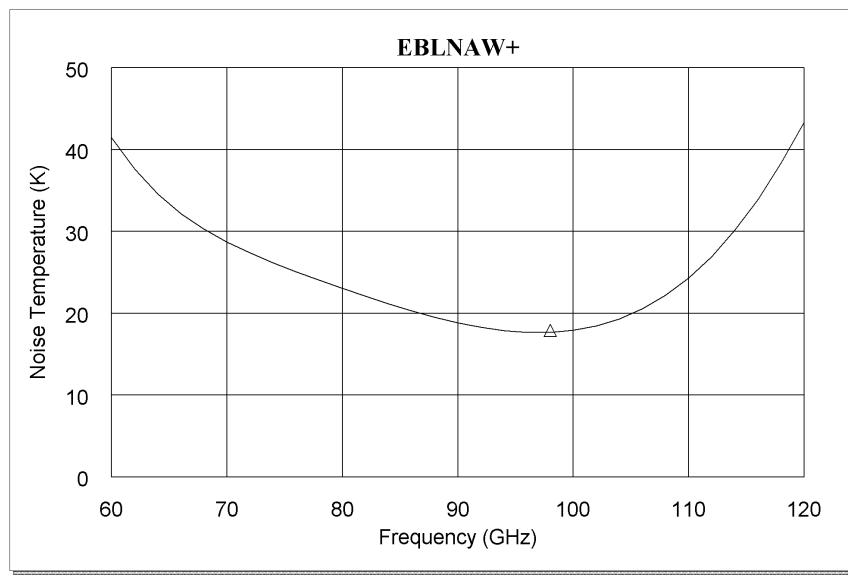
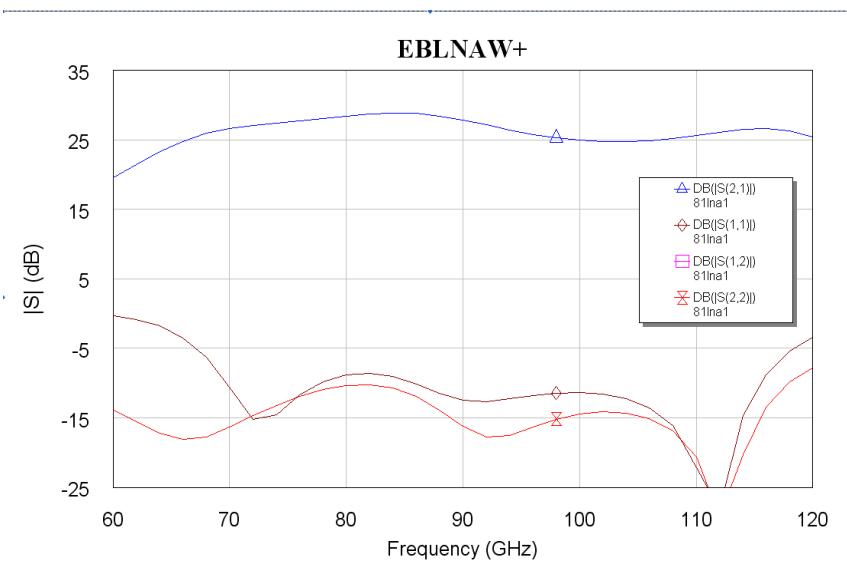


L13: 65 to 34um
L14: 78 to 144um

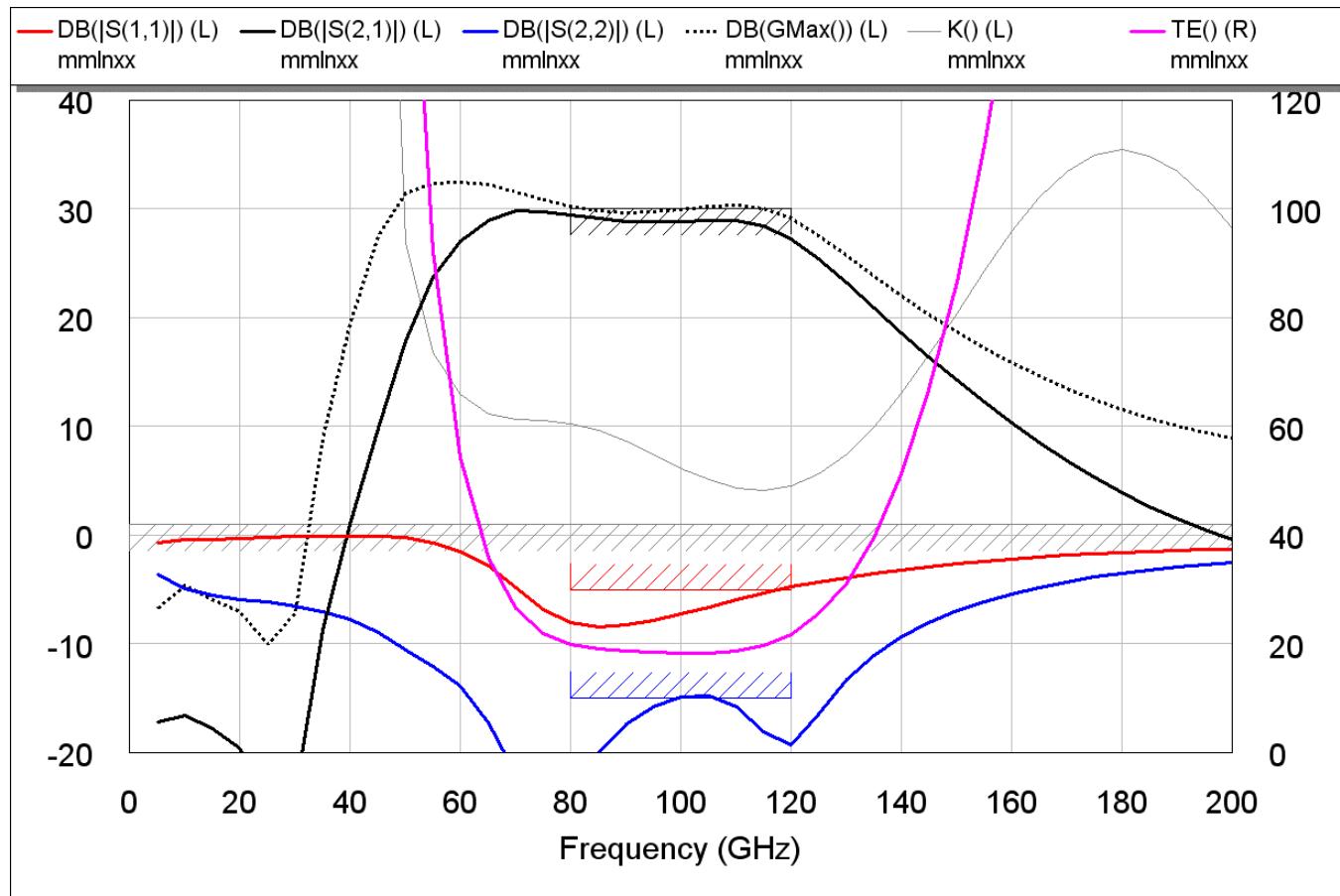
L13
L14



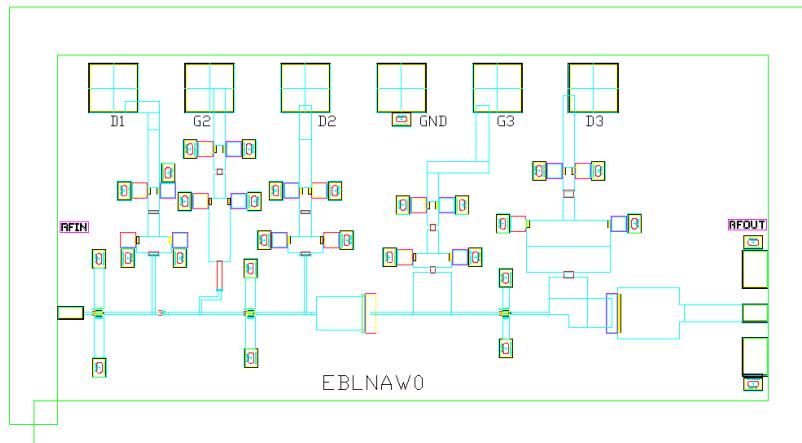
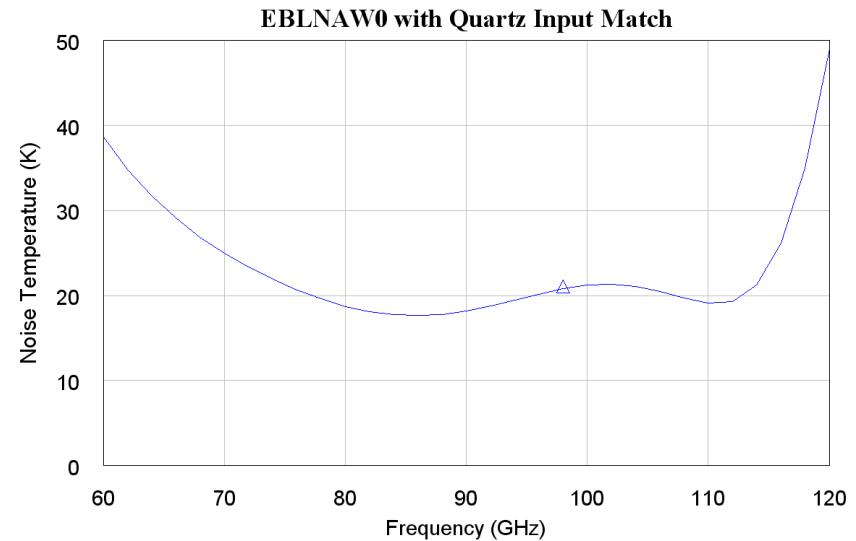
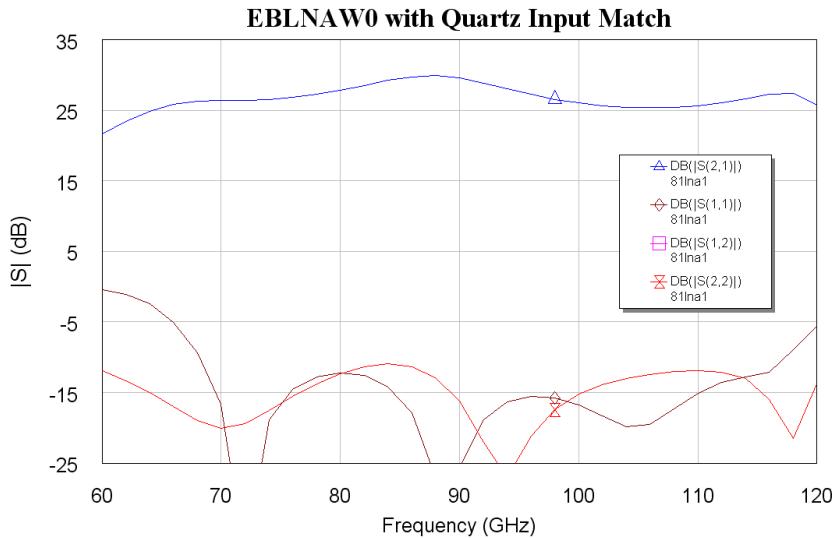
EBLNAW+: Cover full 68-116 GHz band



MMLN100: Cover full 68-116 GHz band



EBLNAW0: A “Tunable” MMIC LNA



Questions / Discussion Points

- Is the process repeatable?
- These results are with 70% channel, what do they look like with 100% channel (higher gm)?
- Operation at 4K
- Ultimate limit for W-band LNA noise temperature
- Comparison to SIS development

